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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
KOCHERGIN ET AL.

Atty. Ref.: 340-81

Serial No. 10/686,519

TC/A.U.: 2872

Filed: 16 October 2003

Examiner:

For: METHOD OF MANUFACTURING A SPECTRAL FILTER FOR GREEN AND LONGER WAVELENGTHS

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July 15, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the listed documents have been considered and made of record in this case.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____

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Sheet 1 of 1

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
340-81	10/686,519
APPLICANT	
KOCHERGIN ET AL.	
FILING DATE	TC/A.U.
16 October 2003	2872

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

		K. Barla et al., "X-Ray Topographic Characterization of Porous Silicon Layers," *J. Cryst. Growth*, **68**, North-Holland, Amsterdam, p. 721-726 (1984)
		B.H. Erne et al., "Porous Etching: A Means to Enhance the Photo response of Indirect Semiconductors," *Adv. Mater.*, **7**, p. 739-742 (1995)
		P.A. Kohl et al., J. Electrochem. Soc., **130 (111)**, "The Photoelectrochemical Oxidation of (100), (111), and (lll) n-InP and n-GaAs," p. 2288-2293 (11/1983)
		Schmuki P. et al., *Physica Status Solidi A*, "Pore Formation on n-InP," **182 (1)**, pp. 51-61, (2000)
		S. Langa et al., "Formation of Porous Layers with Different Morphologies during Anodic Etching of n-InP," *J Electrochem. Soc. Lett.*, **3 (11)**, p. 514-516, (2000).
		S. Langa et al., *Phys. Stat. Sol.* **(A), 195 (3)**, "Electrochemical pore etching in Ge," R4–R6 (2003)
		Macleod H.A., *Thin-Film Optical Filters*, 3rd ed., Institute of Physics Publishing, 2001
		D.J. Lockwood et al., "Optical properties of porous GaAs," *Physica E*, **4**, pp. 102-110 (1999)
		Schmulki, P. et al., "Formation of porous layers on InSb(100) by anodization," *Phys. Stat. Sol.* (a) 197, No. 1, pp. 71-76 (2003)
		Langa, S. et al., "Voltage oscillations – an emergent property at high density pore growth," *Phys. Stat. Sol.* (a) 197, No. 1, pp. 186-191 (2003)

*Examiner		Date Considered	

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.